



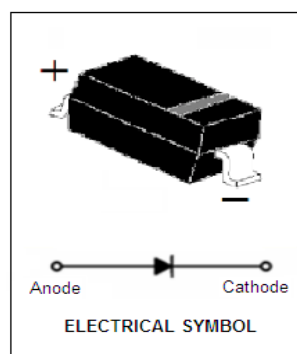
SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOD-123 封装二极管/SOD-123 Plastic-Encapsulate Diodes

B0520LW/B0530W/B0540W (SCHOTTKY DIODES)

特点/Features :

- Low Forward Voltage Drop ;
- Guard Ring Construction for Transient Protection ;
- High Conductance ;
- Also Available in Lead Free Version ;



极限参数/Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	B0520LW	B0530W	B0540W	Unit
Peak Repetitive Reverse Voltage	V_{RRM}				
Working Peak Reverse Voltage	V_{RWM}	20	30	40	V
DC Blocking Voltage	V_R				
RMS Reverse Voltage	$V_{R(RMS)}$	14	20	28	V
Average Rectified Output Current	I_o	500			mA
Forward Surge Current Peak	I_{FSM}	5.5			A
Power Dissipation	P_d	500			mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$	200			°C/mW
Junction Temperature	T_j	125			°C
Storage Temperature	T_{stg}	-55~150			°C
Voltage rate of Change	dv/dt	1000			V/μS

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	B0520LW	B0530W	B0540W	单位
Minimum Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R=250 \mu A$	20			V
		$I_R=200 \mu A$		30		
		$I_R=20 \mu A$			40	
Forward Voltage	V_{F1}	$I_F=0.1A$	0.32	0.375	--	V
	V_{F2}	$I_F=0.5A$	0.385	0.43	0.51	V
	V_{F3}	$I_F=1A$	--	--	0.62	V
Reverse Current	I_{R1}	$V_R=10V$	75	--	--	μA
	I_{R2}	$V_R=15V$	--	20	--	
Reverse Current	I_{R3}	$V_R=20V$	250	--	10	μA
	I_{R4}	$V_R=30V$	--	130	--	
	I_{R5}	$V_R=40V$	--	--	20	
Capacitance Between Terminals	C_T	$V_R=0V, f=1.0MHz$			170	pF

印章/ Marking:

型号	B0520LW	B0530W	B0540W
印章	SD	SE	SF



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典型特性曲线图/Typical Characteristics

